



PATENT: 06354ZP USA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

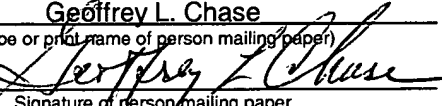
IN RE APPLI-  
CATION OF : SIDDIQUI, ET. AL. : CONFIRM. NO. 2963

SERIAL NO. : 10/730,527 : GRP. ART UNIT: 1755

FILED : 12/08/03 : EXAMINER: MARCHESCHI

FOR : COMPOSITION AND ASSOCIATED METHOD FOR OXIDE  
CHEMICAL MECHANICAL PLANARIZATION

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

<b>CERTIFICATE OF MAILING</b>	
I CERTIFY THAT THIS PAPER (ALONG WITH ANY PAPER REFERRED TO AS BEING ATTACHED OR ENCLOSED) IS BEING DEPOSITED WITH THE UNITED STATES POSTAL SERVICE WITH SUFFICIENT POSTAGE AS FIRST CLASS MAIL IN AN ENVELOPE ADDRESSED TO:	
COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, VA 22313-1450	
ON _____	7 July 2006
	Date
Geoffrey L. Chase	
(Type or print name of person mailing paper)	
	
Signature of person mailing paper	

Sir:

**UPDATED DECLARATION OF JUNAID AHMED SIDDIQUI UNDER RULE 132**

Responsive to the Office Action of 7 April 2006, rejecting Claims 1, 3-9 and 11-18, Applicant submits this updated Declaration of Junaid Ahmed Siddiqui, PhD., the inventor of the Present Invention.

Dr. Siddiqui states:

1. He is a resident of 5720 Turkey Oak Road, Richmond, VA 23237.
2. He is a graduate of Karachi University in Pakistan with a B.S. in Chemistry with honors awarded in 1966, a graduate of the University of Western Ontario, Canada with a M.S. in Photochemistry awarded in 1969, and a graduate of the University of Cincinnati with a Ph.D. in Physical Chemistry awarded in 1973.

3. He was a postdoctoral fellow at the National Aeronautics and Space Administration (NASA) during 1973-75 and a teaching post-doctoral fellow at Virginia Commonwealth University during 1975-76.

4. He was employed by Imperial Chemical Industries from 1976-1997 and was and is employed by E.I. DuPont de Nemours from 1997 to the present. Since 2000 to the present, he has been on assignment to DuPont Air Products NanoMaterials L.L.C., a joint venture between DuPont and Air Products, working in the area of development of new nanoslurry dispersions for chemical mechanical planarization in microelectronic applications. During the period 2000-2004, he was Chief Scientist for this joint venture.

5. He is an inventor in the present Application Serial No. 10/730,527 filed December 8, 2003 for "Composition and Associated Method for Oxide Chemical Mechanical Planarization".

6. He has read and understood the present Application Serial No. 10/730,527 filed December 8, 2003 for "Composition and Associated Method for Oxide Chemical Mechanical Planarization".

7. He has read and understood the **currently** cited references of record; US 5,993,686; US 6,471,735; US 6,468,913; and US 2003/0228762 as well as the following **earlier** cited references of record: US 6,736,905; US 6,471,735; US 5,993,686; and McCutcheon's Vol. 1, Emulsifier & Detergents, 1999, N. American Edition.

8. He has read and understood the Examiner's Office Action **dated 7 April 2006**.

9. With the objective of obtaining unexpected results that are clear and convincing with regard to the Invention defined in this Patent Application (as indicated as being desirable on Page 6 of the 7 April 2006 Office Action), he directed experimental work on testing chemical mechanical planarization (CMP) samples that contain silica, ammonium fluoride, and either an inventive hydroxy alkyne surfactant (i.e., Surfynol® 104e) or an unclaimed ethoxylated alkyne surfactant (i.e., Surfynol® 465), as well as one example (#3)

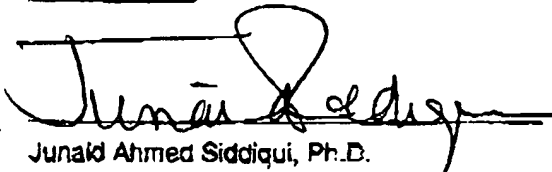
USSN 10/730,527  
063542P USA  
Page 3

where silica at pH 10.5 is the polishing medium with ammonium fluoride and surfactant being absent. The experimental work done is summarized in attached Table 2 as Examples 3-7. This experimental work was reported in Dr. Siddiqui's Declaration filed 21 February 2006 and is updated with regard to Dr. Siddiqui's evaluation of additional prior art and the current rejection per Paragraphs 7 and 8, above.

10. He is of the opinion, as an expert skilled in the art, that the results of this further experimental work, as summarized in Table 2 (including footnotes #, ##, and !!), clearly indicate that use of compositions in oxide CMP containing hydroxy alkyne surfactant plus ammonium fluoride affords defectivity levels on the polished wafers that are at least 10-fold lower than corresponding defectivity levels measured under comparable conditions for compositions in oxide CMP containing ethoxylated alkyne surfactant plus ammonium fluoride. It is his opinion that these results show an unexpected and significant result of the present invention over the prior art.

11. He states that he has been warned that willful false statements and the like are punishable by fine or imprisonment, or both (18 USC 1001) and may jeopardize the validity of the application or any patent issuing thereon and that all statements made of his own knowledge are true and that all statements made on information and belief are believed to be true.

**DECLARANT:**

  
Junaid Ahmed Siddiqui, Ph.D.

Date 7/5/2006

Attachment: Table 2

**Table 2: Oxide Removal rates with Pre-HF and post-HF Dip Defect Counts For TEOS Polished Wafers**

Sample	Example 3	Example 4	Example 5	Example 6	Example 7
Silca (polysilicate free), wt %	30	30	30	30	30
Ammonium fluoride	0	0.1	0.1	0	0.1
Surfynol® 465 (An ethoxylated alkyne)	0	0	0	0	0.01
Surfynol® 104E (An acetylenic diol)	0	0	0.01	0.01	0
pH	10.5	10.5	10.5	10.5	10.5
Pre-HF Defect count at 0.13 micron *	360	66	36	133	506
Pre-HF Defect count at 0.16micron **	26	3	2	8	22
Post -HF Defect count at 0.16 micron***	296	16	11	42	116
Post -HF Defect count at 0.13 micron***	5940	803	438	1618	6158
Removal rates of oxide at 7 PSI (A/min)	4541	4575	4503	4204	4468

\*, and \*\*, based on Table 1 defect count, post-HF defect in Table 2 was calculated from the ratio of pre-HF defect count and post-HF defect count, Ratio of pre-HF defect count to post HF defect count was 11.4 at 0.18 micron, and 16.5 at 0.13 micron whereas HF containing variant, pre to post HF ratio was 5.3 at 0.18 micron and 12.17 at 0.13 micron.

\*\*\* Defect counts were obtained at 0.13 micron resolution (as had been obtained before in Table 1 in the original application) and at 0.16 micron resolution instead of 0.18 micron done in the original application; Applicant believes this is close enough for this (new) Table 2 shown above. Also, Applicant did not make use in this present work of a post-HF dip test due to safety issues, as it requires the use of large quantities of HF solution; consequently, Applicant was not able to produce experimentally-determined post-HF defect data in Table 2 (as had been done in the filed application in Table 1). However, Applicant was able to calculate the ratio of pre-HF to post- HF defect count from Table 1, which Applicant has earlier found to be approximately constant from sample to sample. Applicant has used these ratios (as indicated above) to calculate estimated post-HF defect counts in Table 2, which Applicant believes to be approximately correct.